

Analysis of deep level system transformation by photoionization spectroscopy

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The photoconductivity spectrum in extrinsic region was measured in irradiated Si samples at 18 K temperature. The samples were treated by isochronal annealing in a range 80-250 C. The deep levels were resolved by use of Lucovsky model. A series of levels was observed and a number of deep centers and their contribution on the photoconductivity were dependent on annealing. The comparison of photoconductivity spectra data and the results obtained by DLTS and TSC in other groups in the same series of samples was performed.

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